



STS6PF30L

P-CHANNEL 30V - 0.027 Ω - 6A SO-8 STripFET™ POWER MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|-----------|------------------|---------------------|----------------|
| STS6PF30L | 30 V | <0.030 Ω | 6 A |

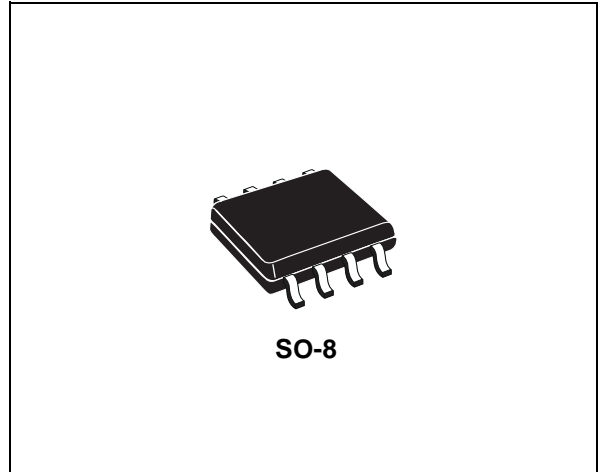
- TYPICAL R_{DS(on)} = 0.027 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE

DESCRIPTION

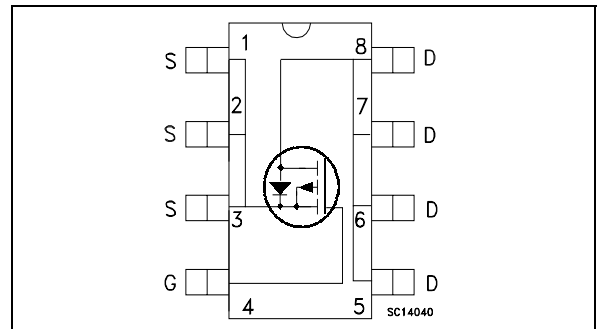
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- MOBILE PHONE APPLICATIONS
- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|-------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 30 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 30 | V |
| V _{GS} | Gate- source Voltage | ± 16 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 6 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 3.8 | A |
| I _{DM} (●) | Drain Current (pulsed) | 24 | A |
| P _{tot} | Total Dissipation at T _C = 25°C | 2.5 | W |

(●) Pulse width limited by safe operating area.

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Note: For the P-CHANNEL MOSFET the actual polarity of the gate, drain and source voltages and current has to be reversed

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STS6PF30L

THERMAL DATA

| | | | | |
|------------------|--|-----|------------|------|
| Rthj-amb | Thermal Resistance Junction-ambient | Max | 50 | °C/W |
| T _j | Maximum Lead Temperature For Soldering Purpose | Typ | 150 | °C |
| T _{stg} | storage temperature | | -55 to 150 | °C |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 16 V | | | ±100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|----------------|----------------|--------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} I _D = 250 μA | 1 | 1.6 | 2.5 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10 V I _D = 3 A V _{GS} = 5 V I _D = 3 A | | 0.027 0.034 | 0.030 0.042 | Ω Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|---|------|------|------|------|
| g _{fs} (*) | Forward Transconductance | V _{DS} =10 V I _D =3 A | | 12 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 1670 | | pF |
| C _{OSS} | Output Capacitance | | | 345 | | pF |
| C _{rSS} | Reverse Transfer Capacitance | | | 120 | | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON(*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|--|------|------------------|------|----------------|
| $t_{d(on)}$ t_r | Turn-on Delay Time Rise Time | $V_{DD} = 15\text{ V}$ $I_D = 3\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, Figure 1) | | 62 140 | | ns ns |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 24\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 5\text{ V}$ (see test circuit, Figure 2) | | 21 3.9 8.6 | 28 | nC nC nC |

SWITCHING OFF(*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------|----------------------------------|--|------|----------|------|----------|
| $t_{d(off)}$ t_f | Turn-off Delay Time Fall Time | $V_{DD} = 24\text{ V}$ $I_D = 3\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 5\text{ V}$ (Resistive Load, Figure 1) | | 57 19 | | ns ns |

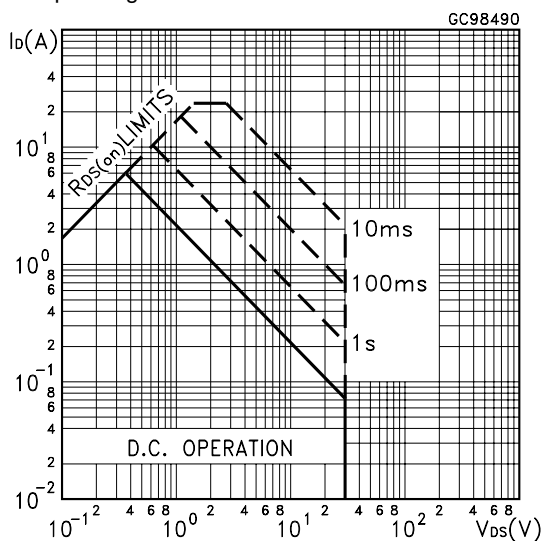
SOURCE DRAIN DIODE(*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|-------------------|--------|---------------|
| I_{SD} $I_{SDM} (\bullet)$ | Source-drain Current Source-drain Current (pulsed) | | | | 6 4 | A A |
| $V_{SD} (*)$ | Forward On Voltage | $I_{SD} = 6\text{ A}$ $V_{GS} = 0$ | | | 1.2 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 6\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 3) | | 37 46.3 2.5 | | ns nC A |

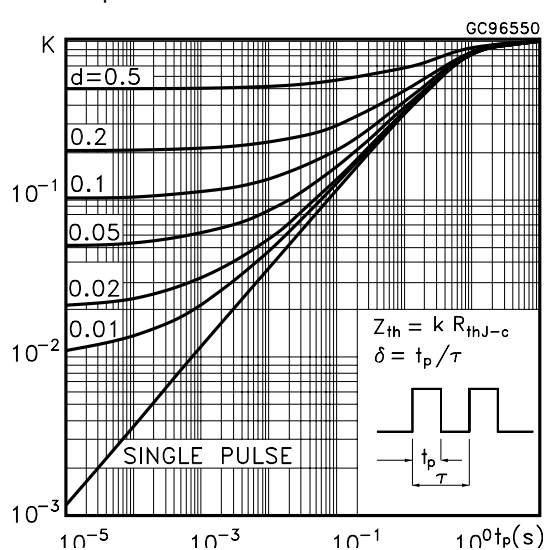
(*)Pulse width $\leq 300\ \mu\text{s}$, duty cycle 1.5 %.

(●)Pulse width limited by T_{JMAX}

Safe Operating Area

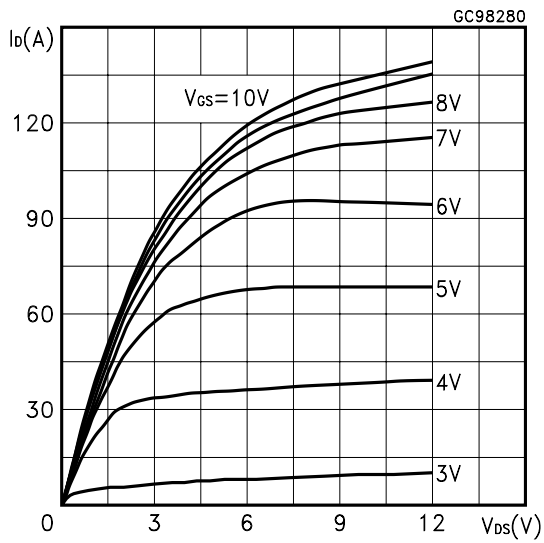


Thermal Impedance

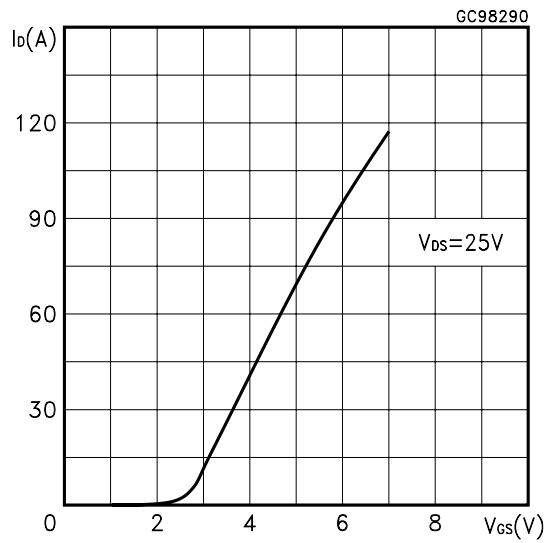


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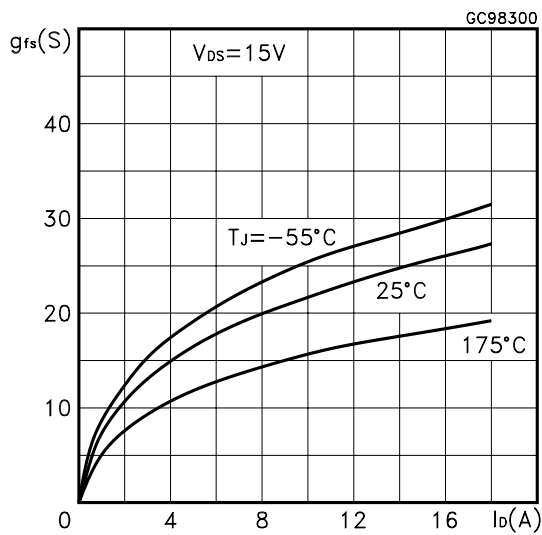
Output Characteristics



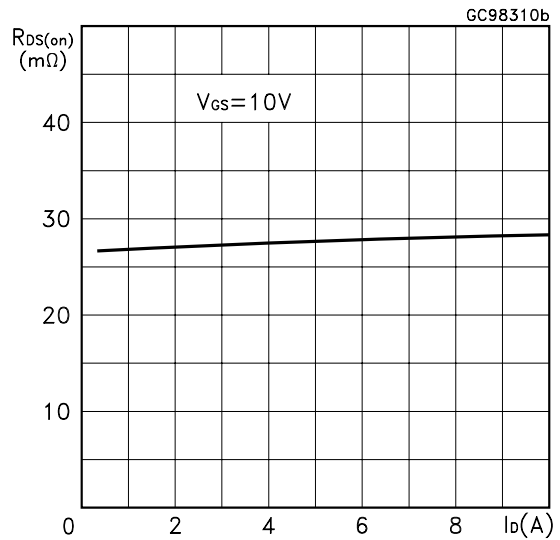
Transfer Characteristics



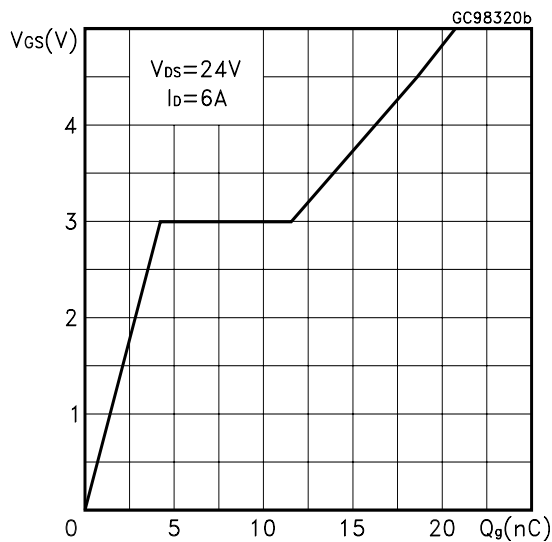
Transconductance



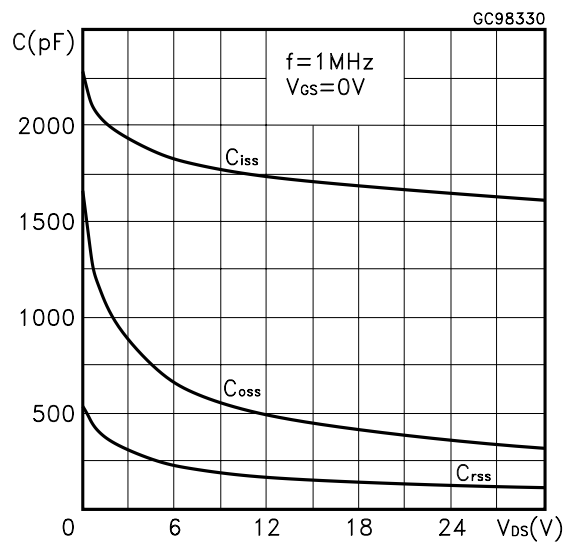
Static Drain-source On Resistance



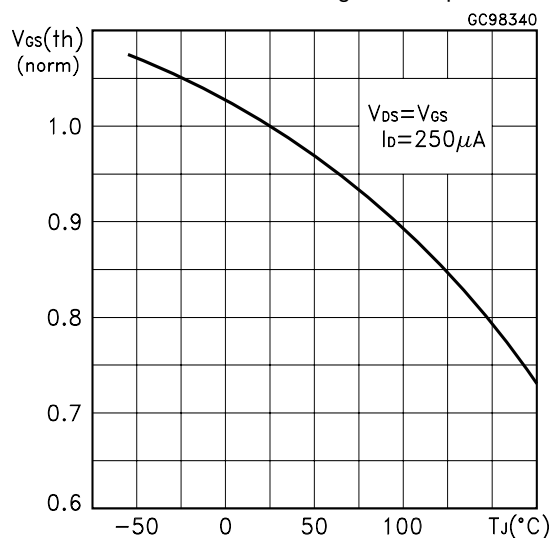
Gate Charge vs Gate-source Voltage



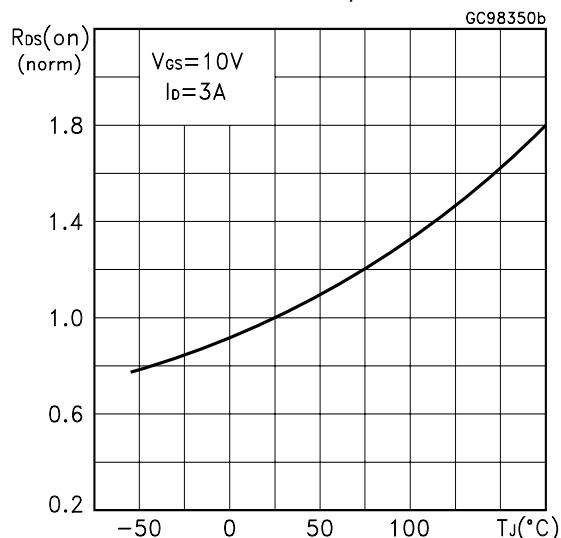
Capacitance Variations



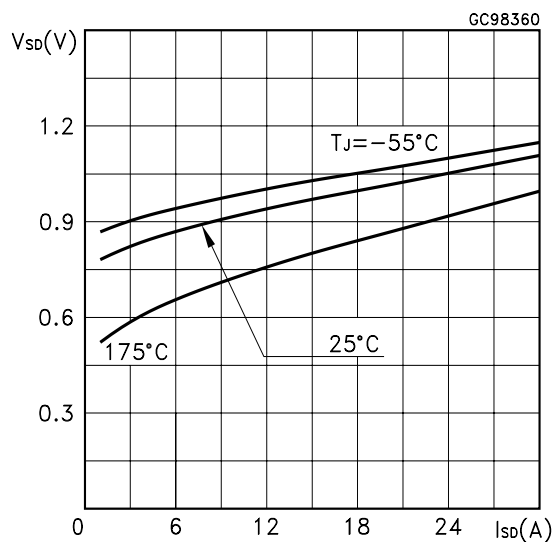
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature

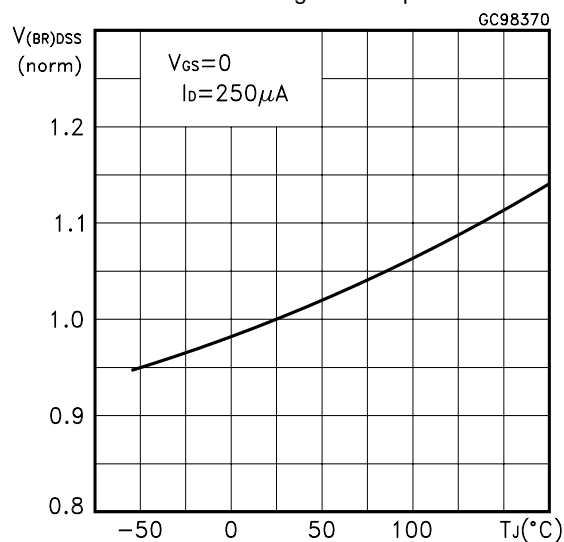


Fig. 1: Switching Times Test Circuits For Resistive Load

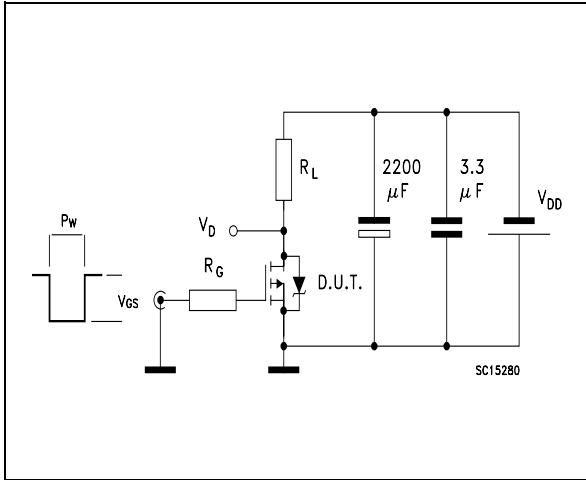


Fig. 2: Gate Charge test Circuit

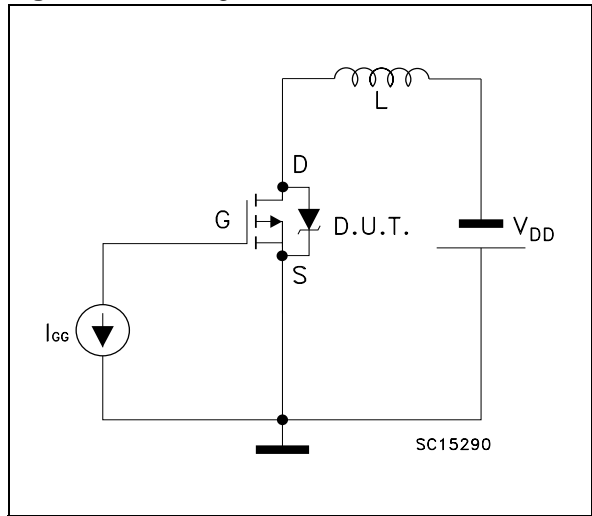
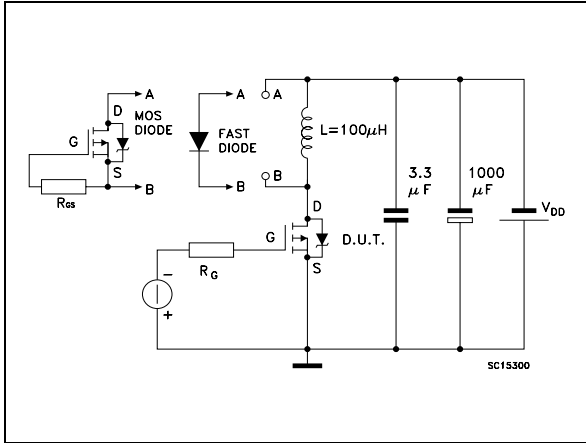
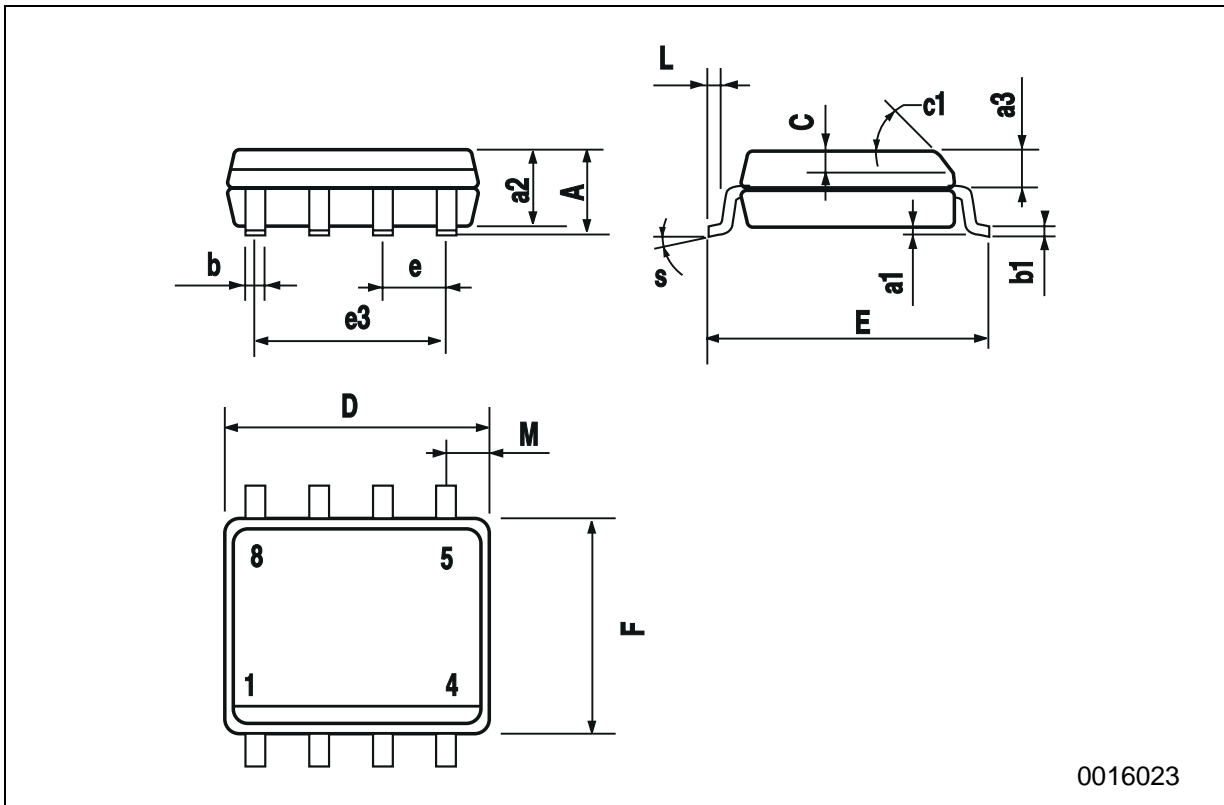


Fig. 3: Test Circuit For Diode Recovery Behaviour



SO-8 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-----------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 1.75 | | | 0.068 |
| a1 | 0.1 | | 0.25 | 0.003 | | 0.009 |
| a2 | | | 1.65 | | | 0.064 |
| a3 | 0.65 | | 0.85 | 0.025 | | 0.033 |
| b | 0.35 | | 0.48 | 0.013 | | 0.018 |
| b1 | 0.19 | | 0.25 | 0.007 | | 0.010 |
| C | 0.25 | | 0.5 | 0.010 | | 0.019 |
| c1 | 45 (typ.) | | | | | |
| D | 4.8 | | 5.0 | 0.188 | | 0.196 |
| E | 5.8 | | 6.2 | 0.228 | | 0.244 |
| e | | 1.27 | | | 0.050 | |
| e3 | | 3.81 | | | 0.150 | |
| F | 3.8 | | 4.0 | 0.14 | | 0.157 |
| L | 0.4 | | 1.27 | 0.015 | | 0.050 |
| M | | | 0.6 | | | 0.023 |
| S | 8 (max.) | | | | | |



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